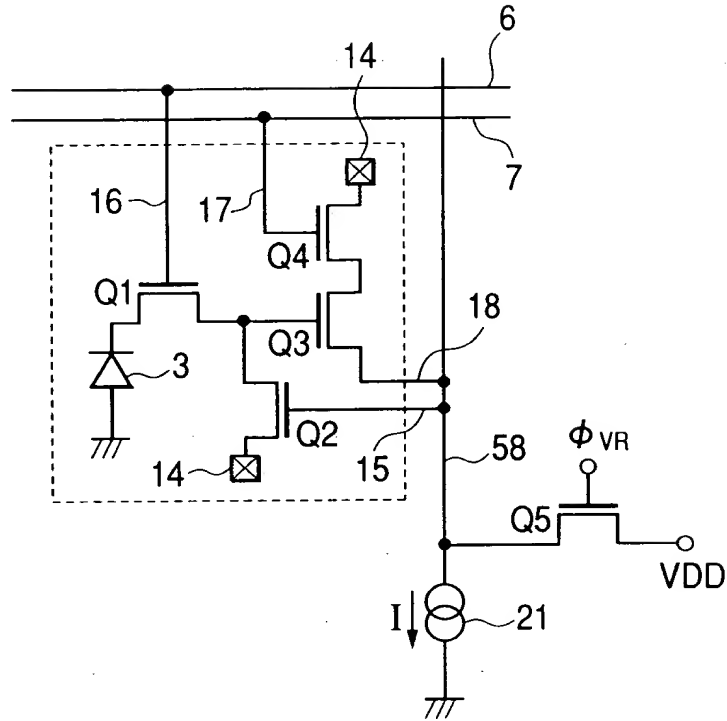
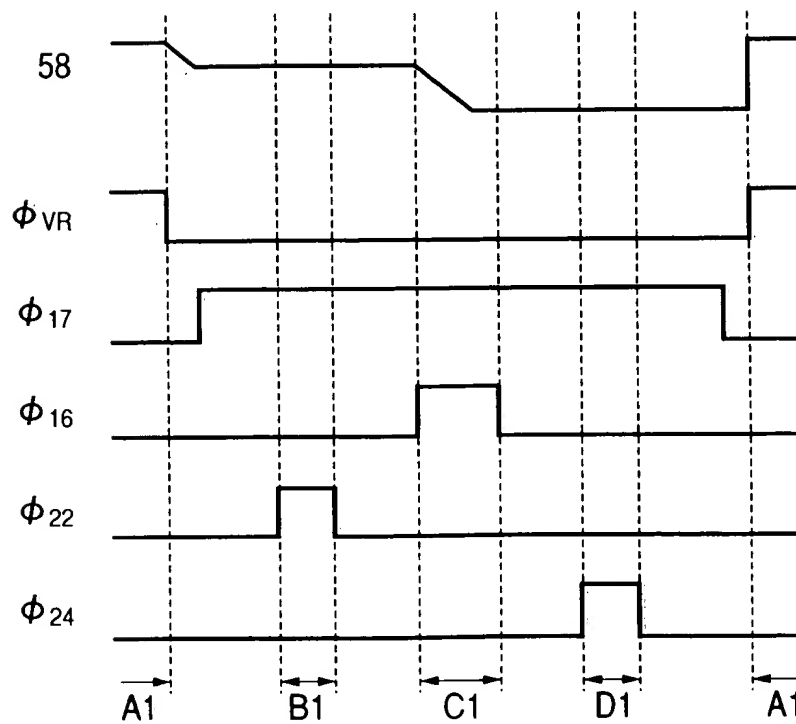


FIG. 1**FIG. 2**

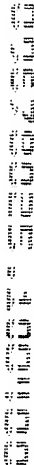
[illegible]

FIG. 4

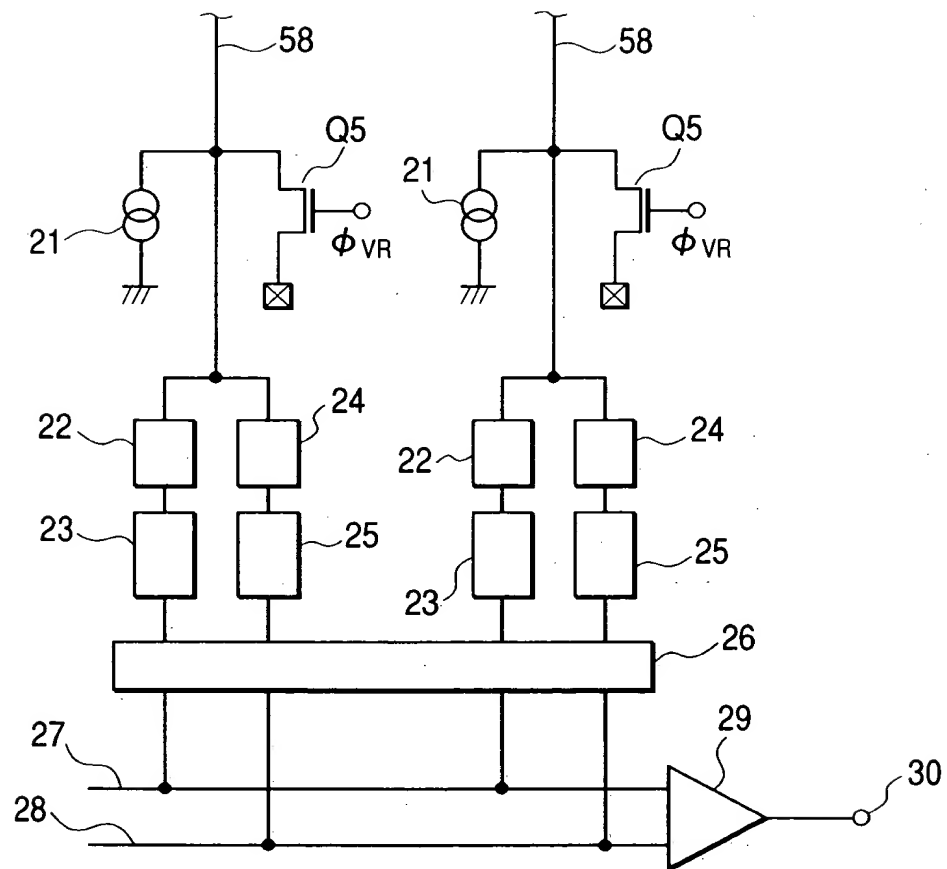


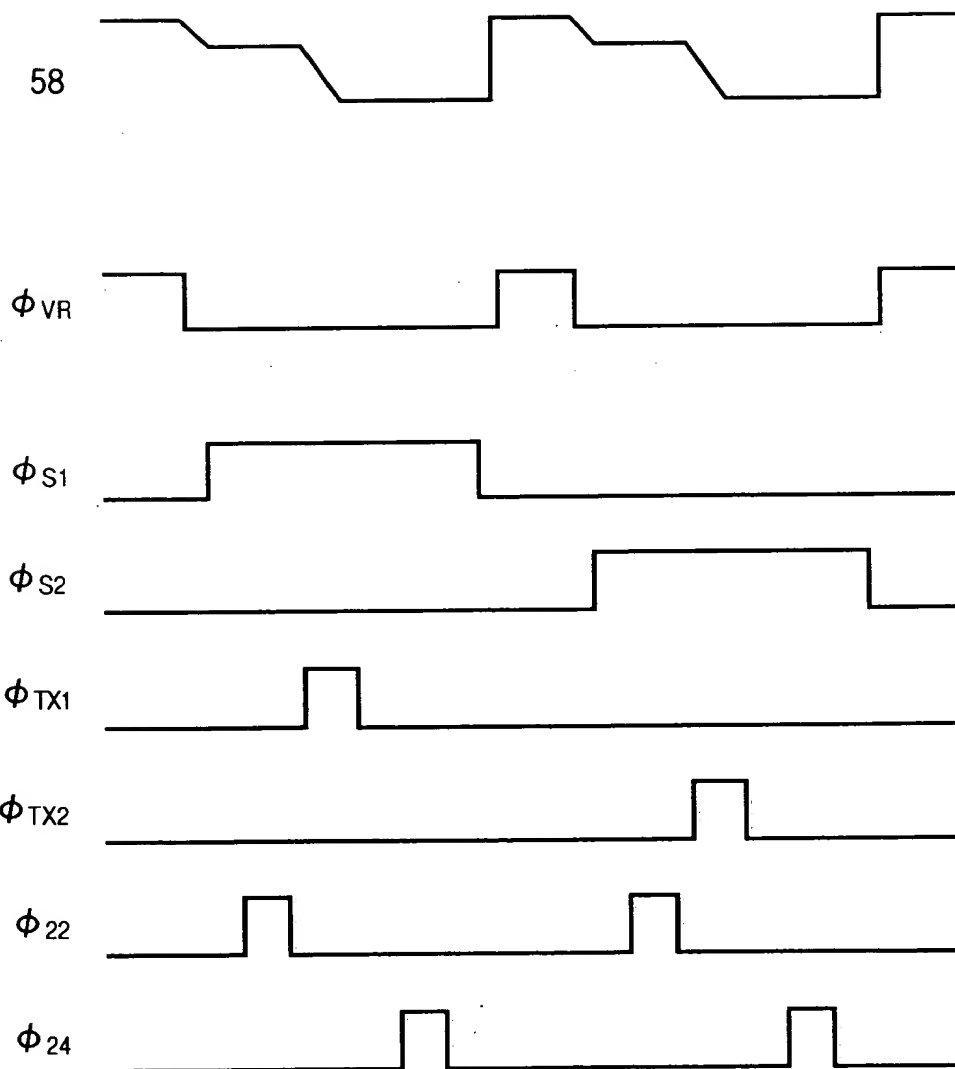
FIG. 5

FIG. 6

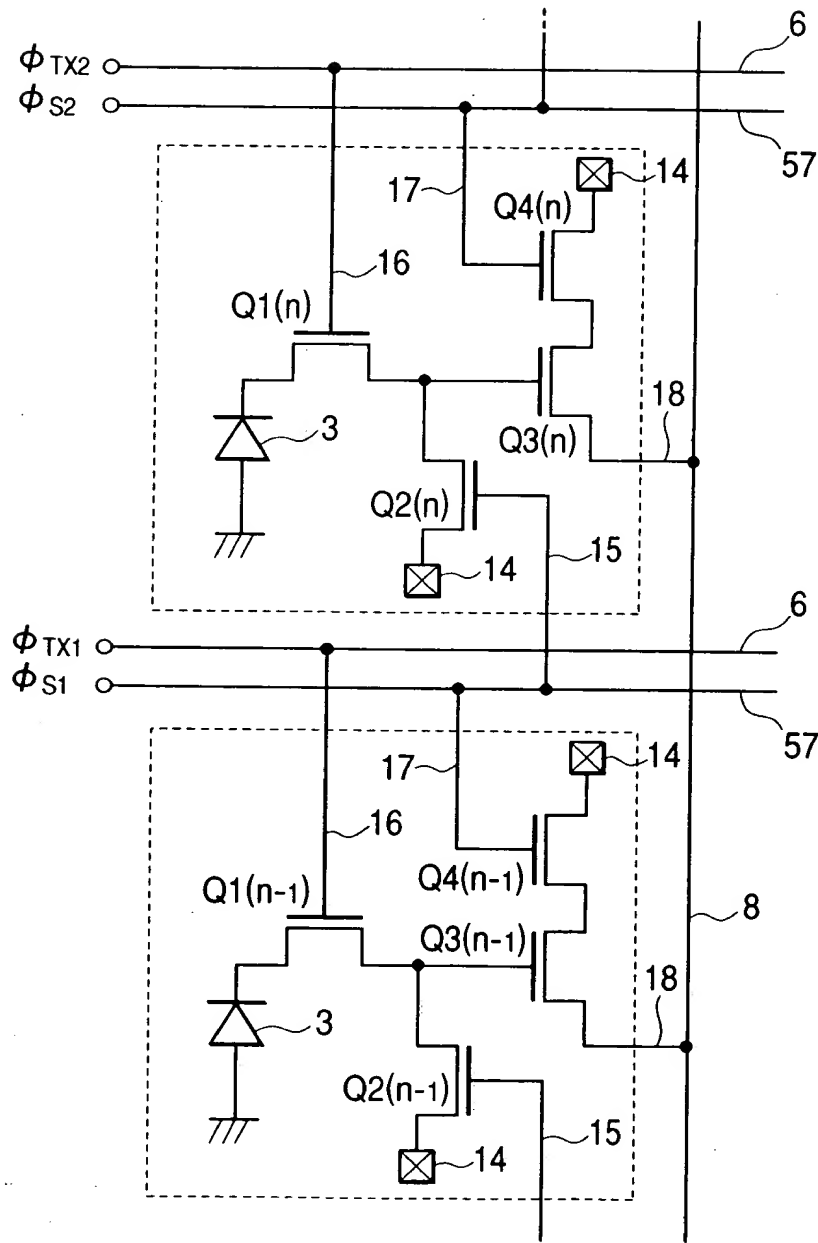
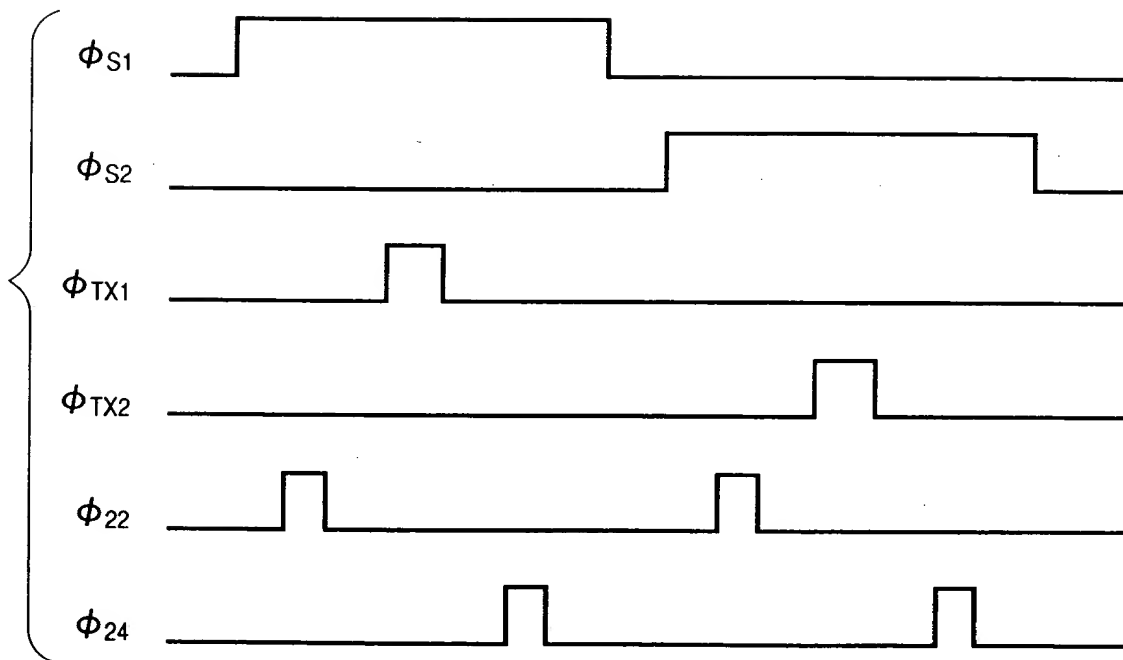
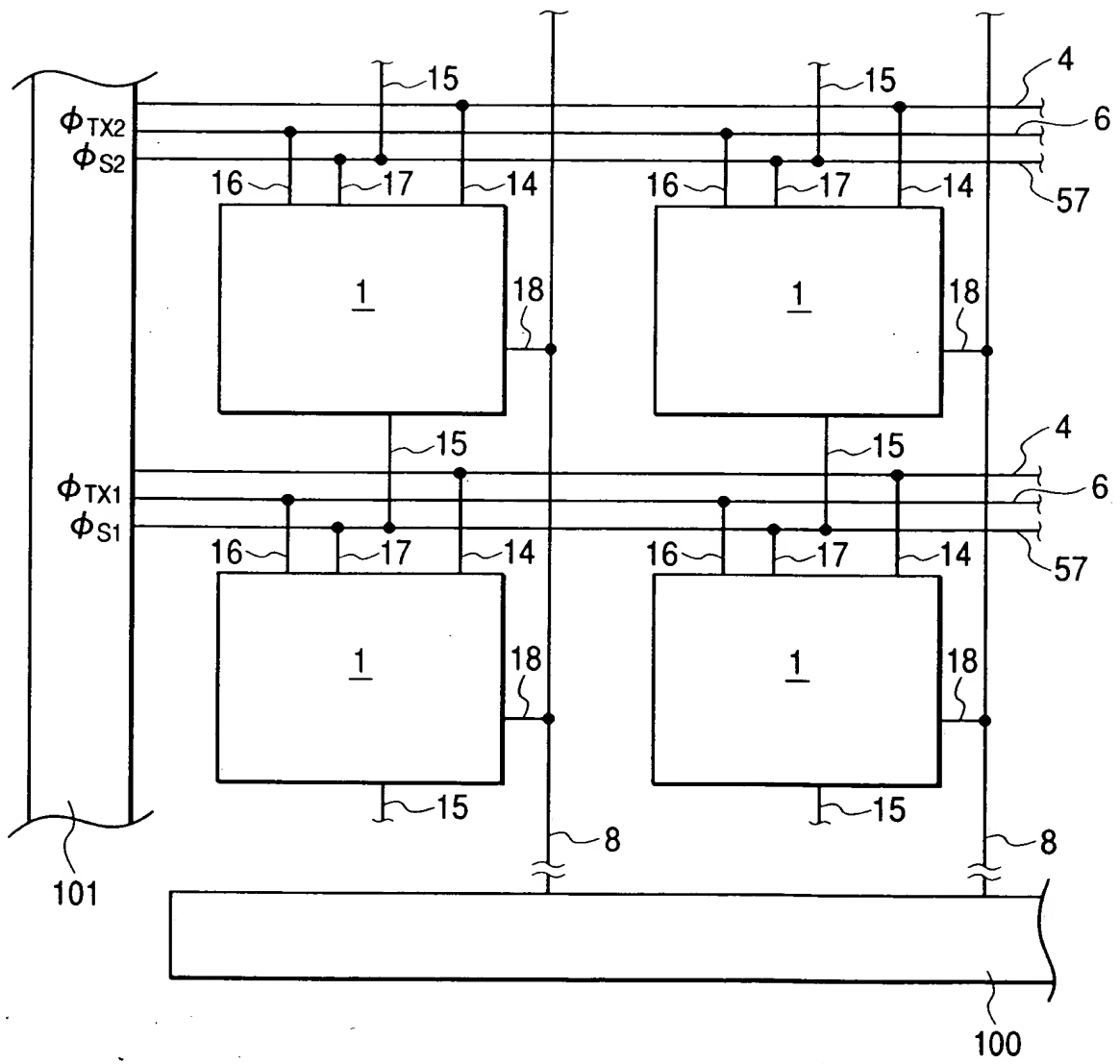


FIG. 7

[illegible]

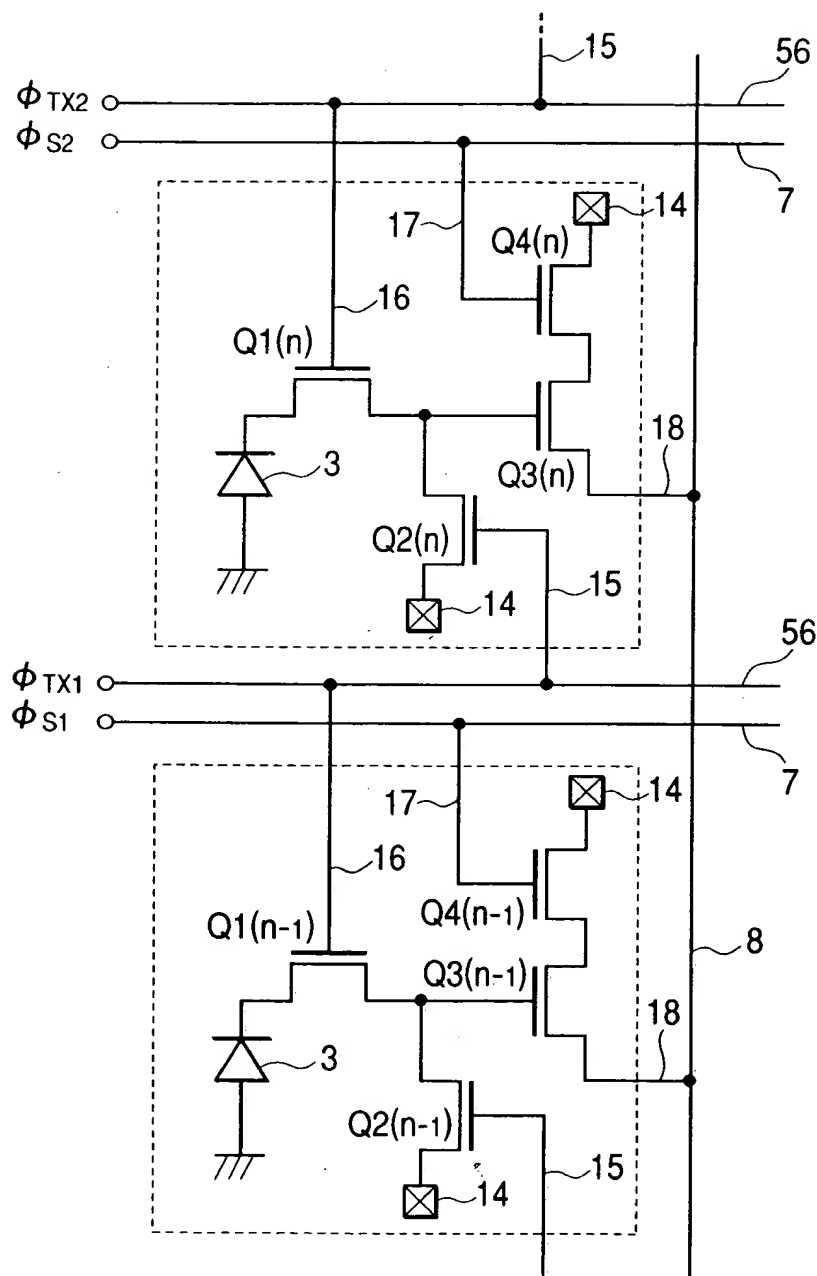
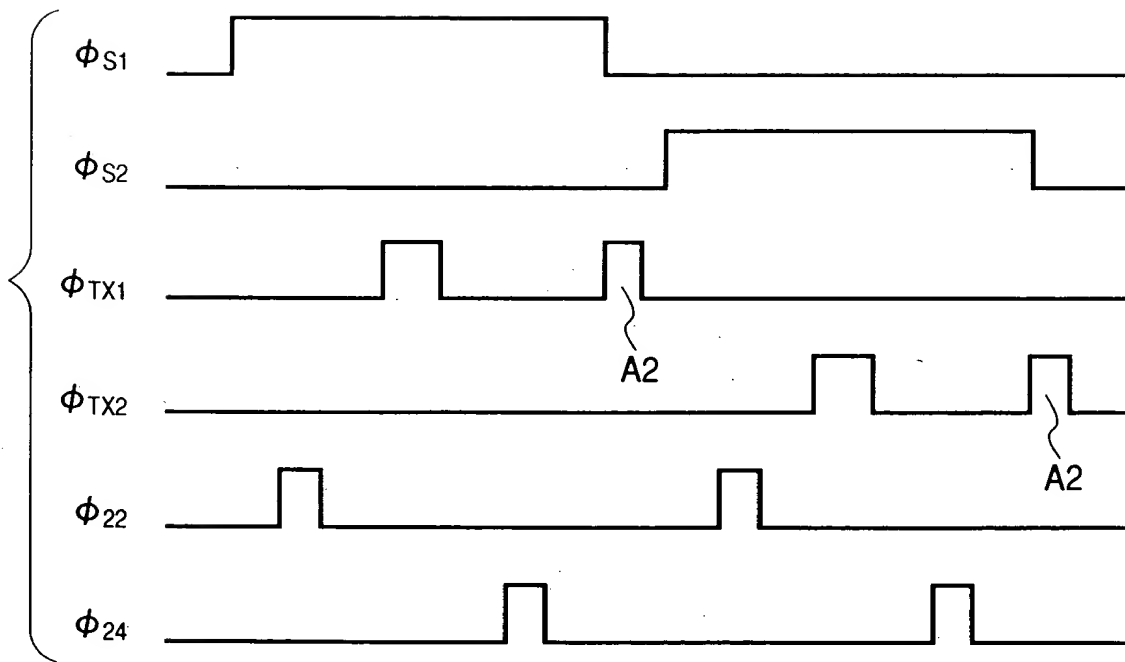
[illegible]

FIG. 10



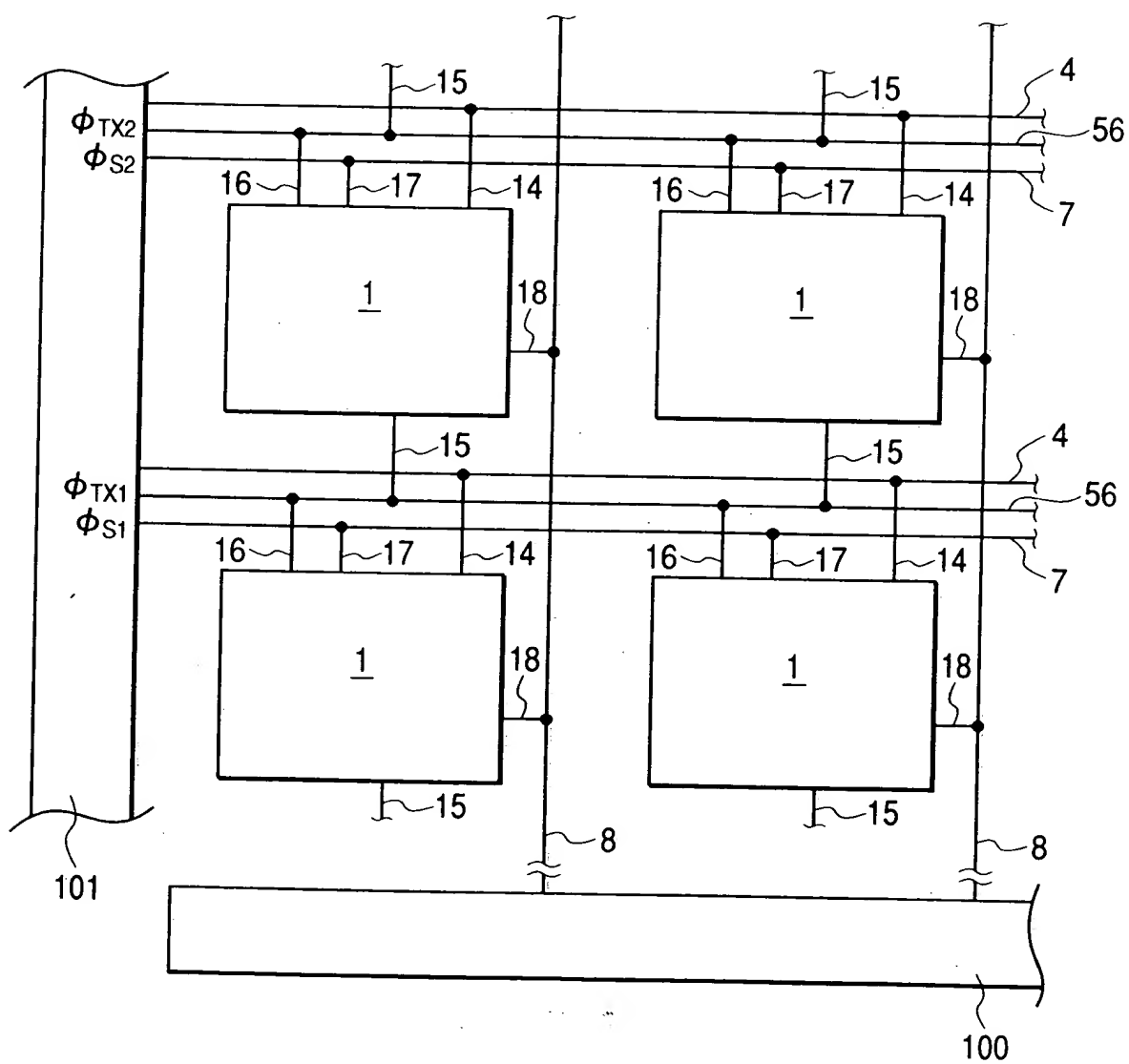
[illegible]

FIG. 12

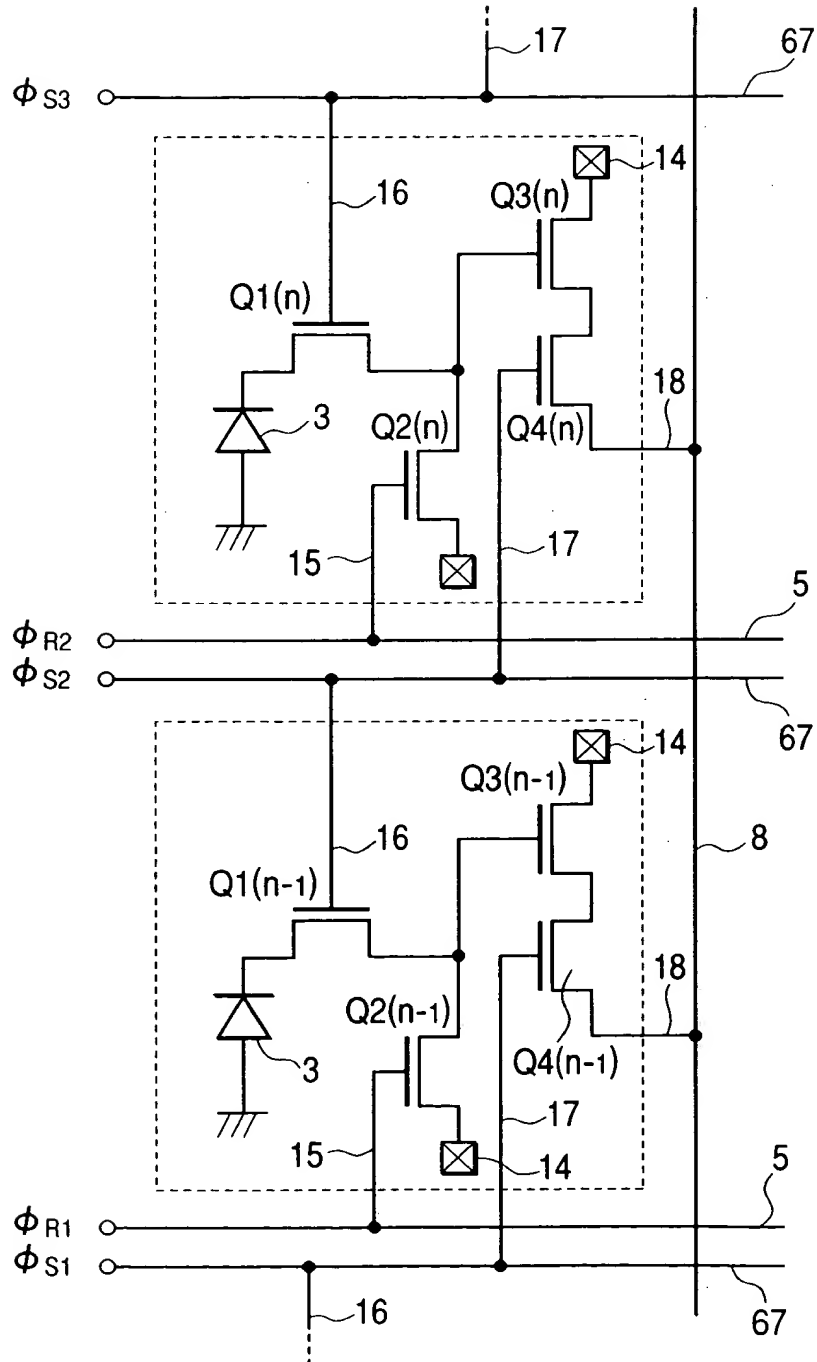


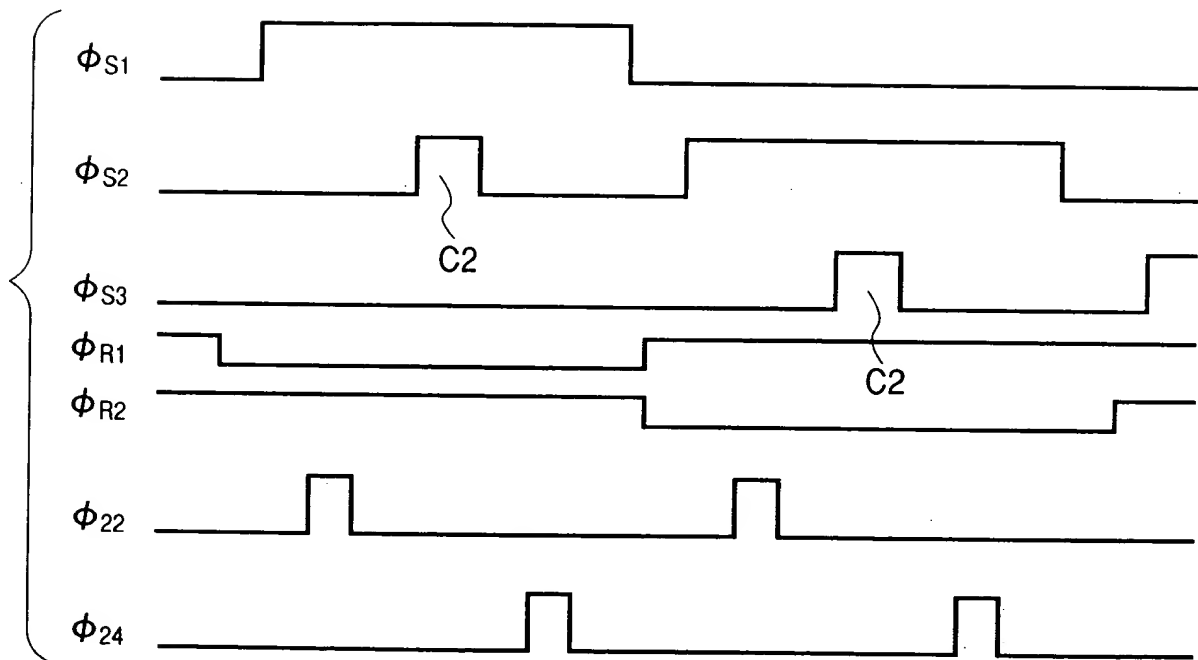
FIG. 13

FIG. 14

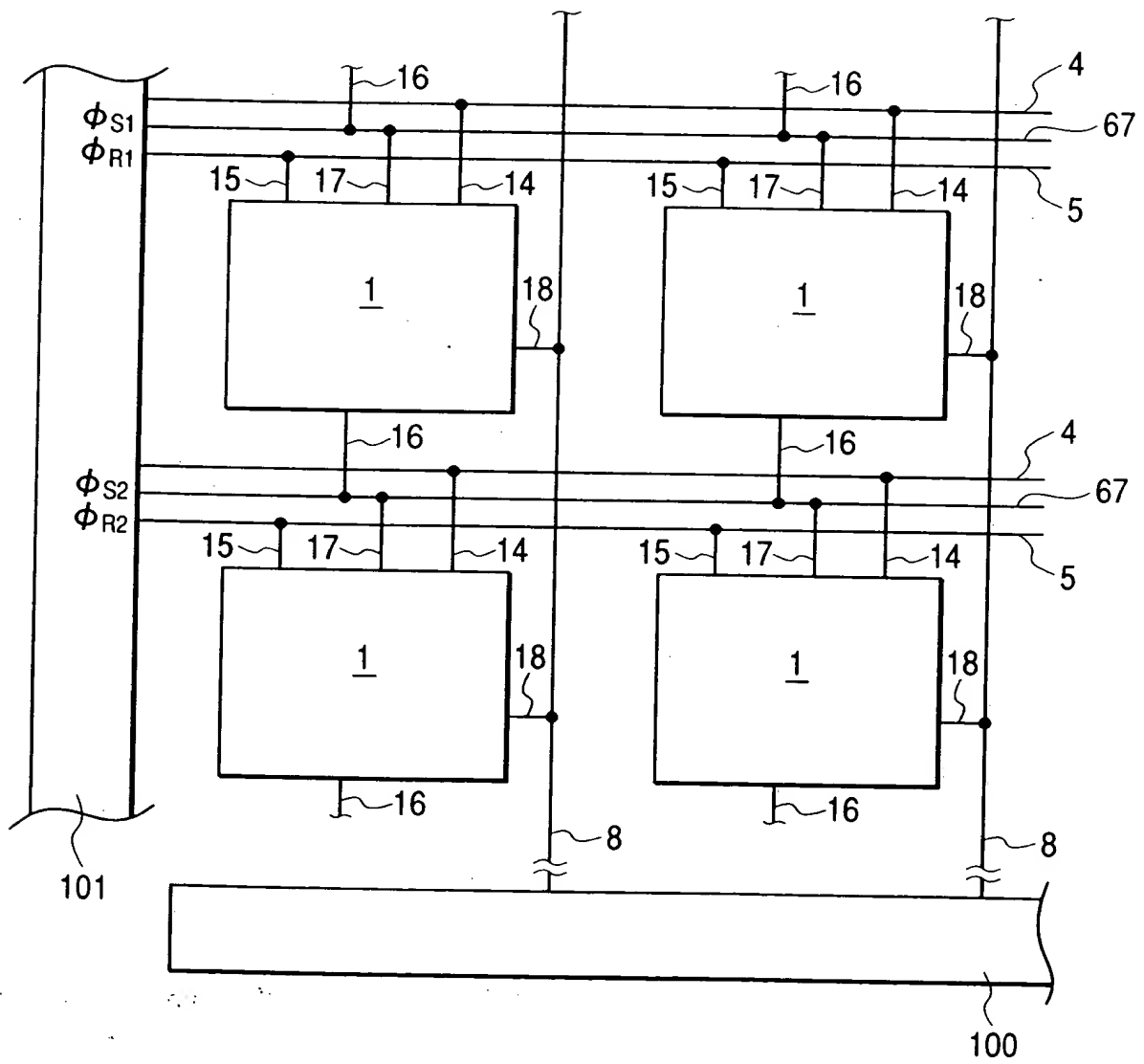


FIG. 15

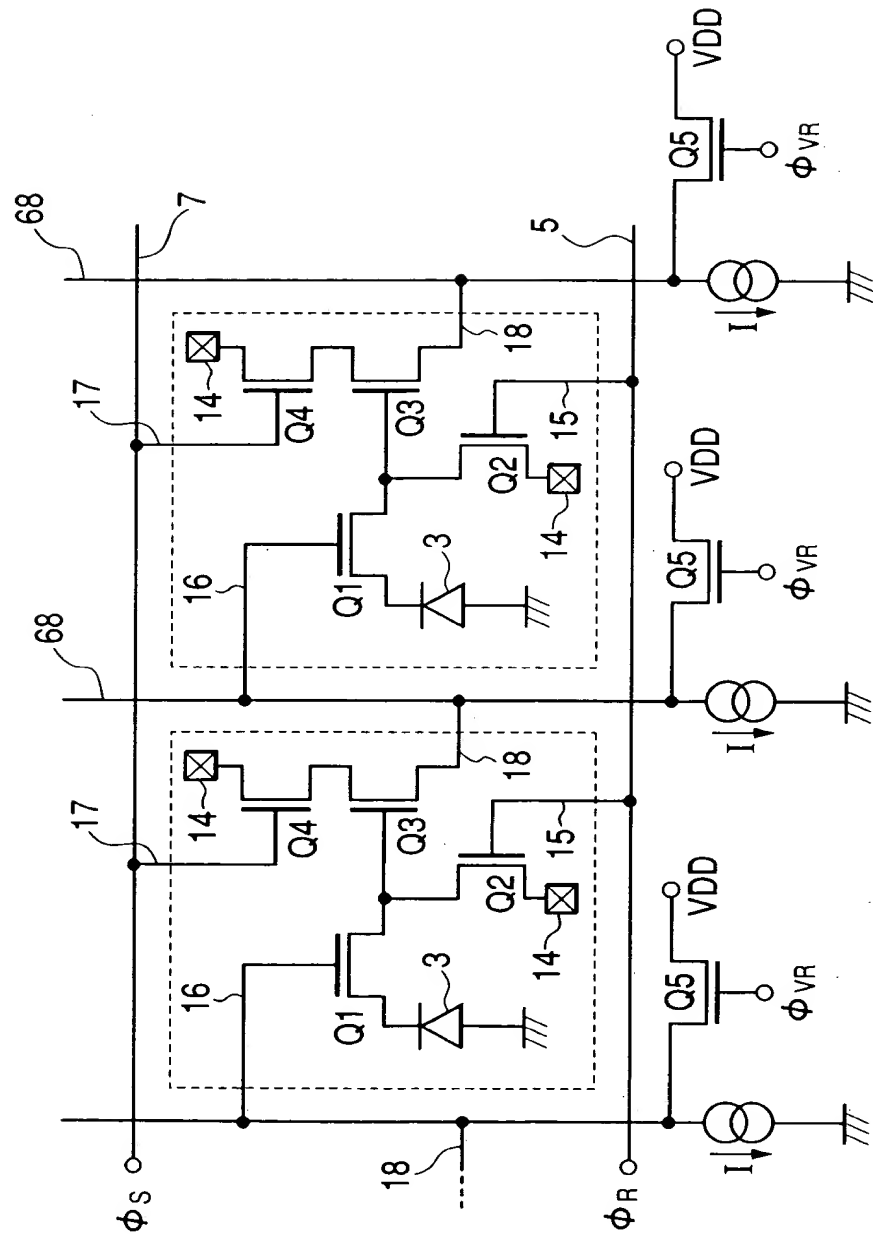


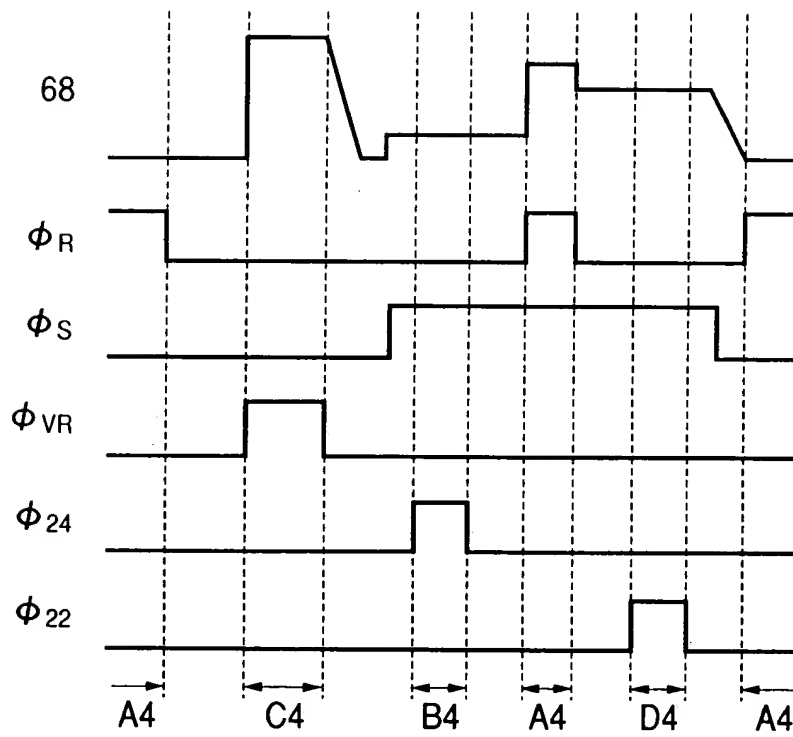
FIG. 16

FIG. 17

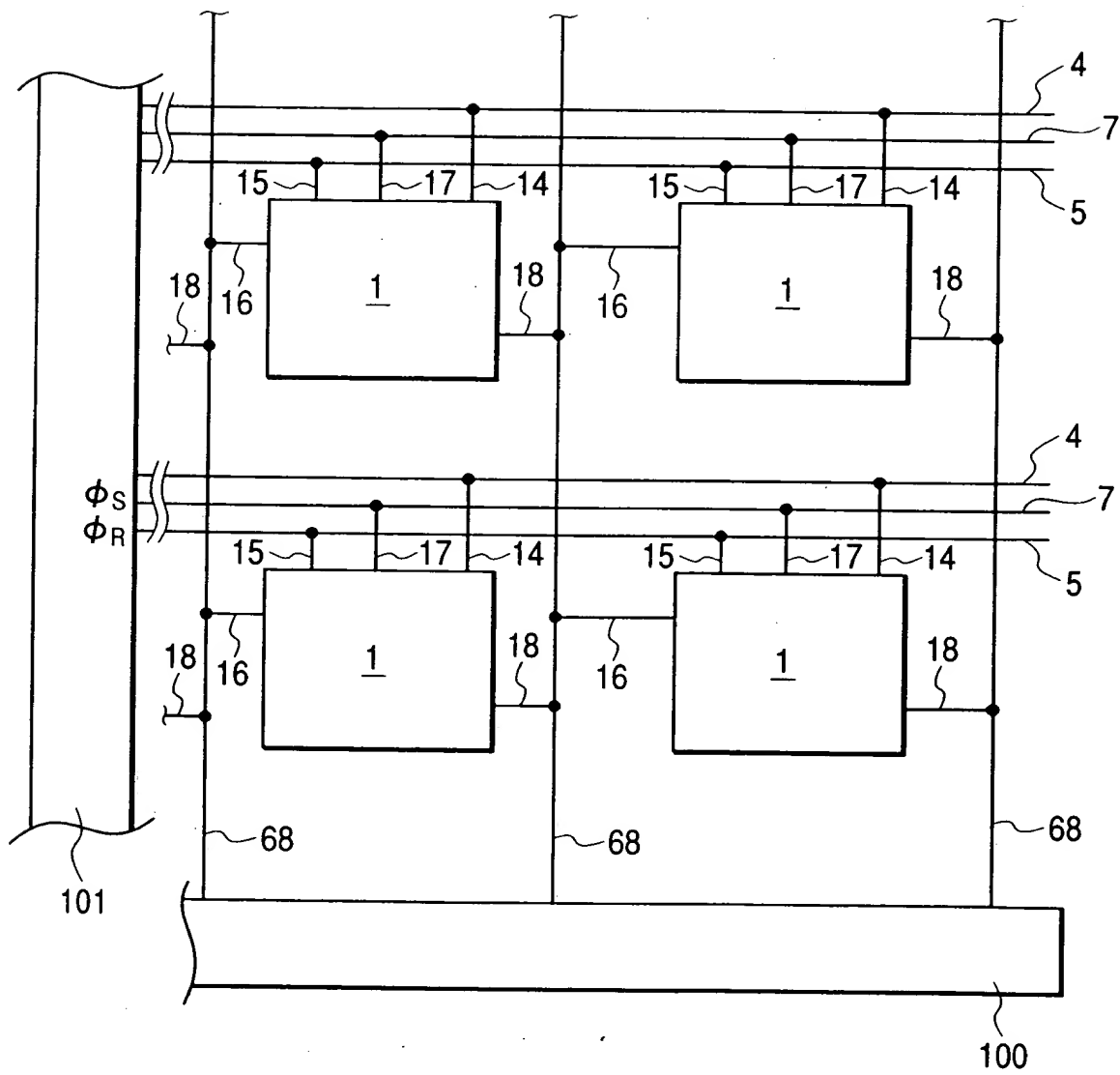


FIG. 18

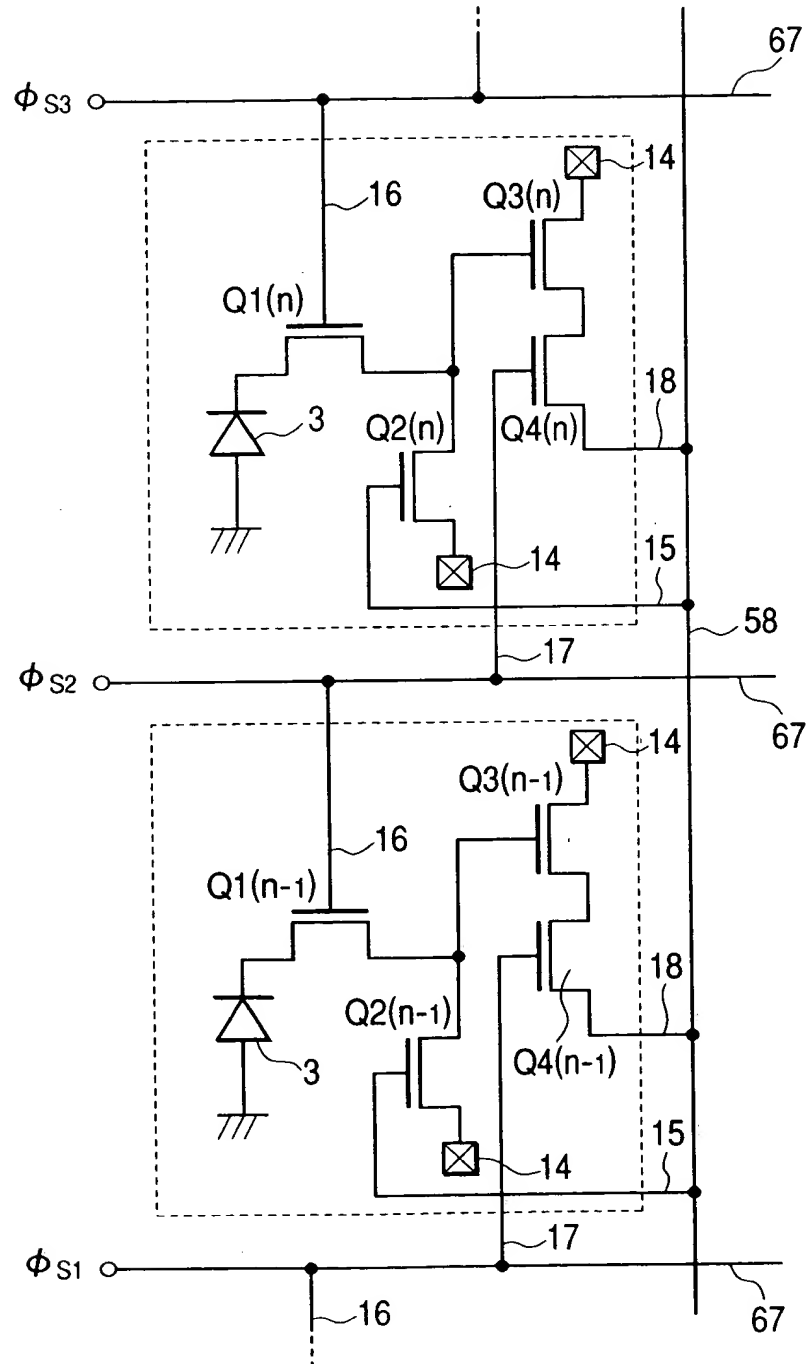


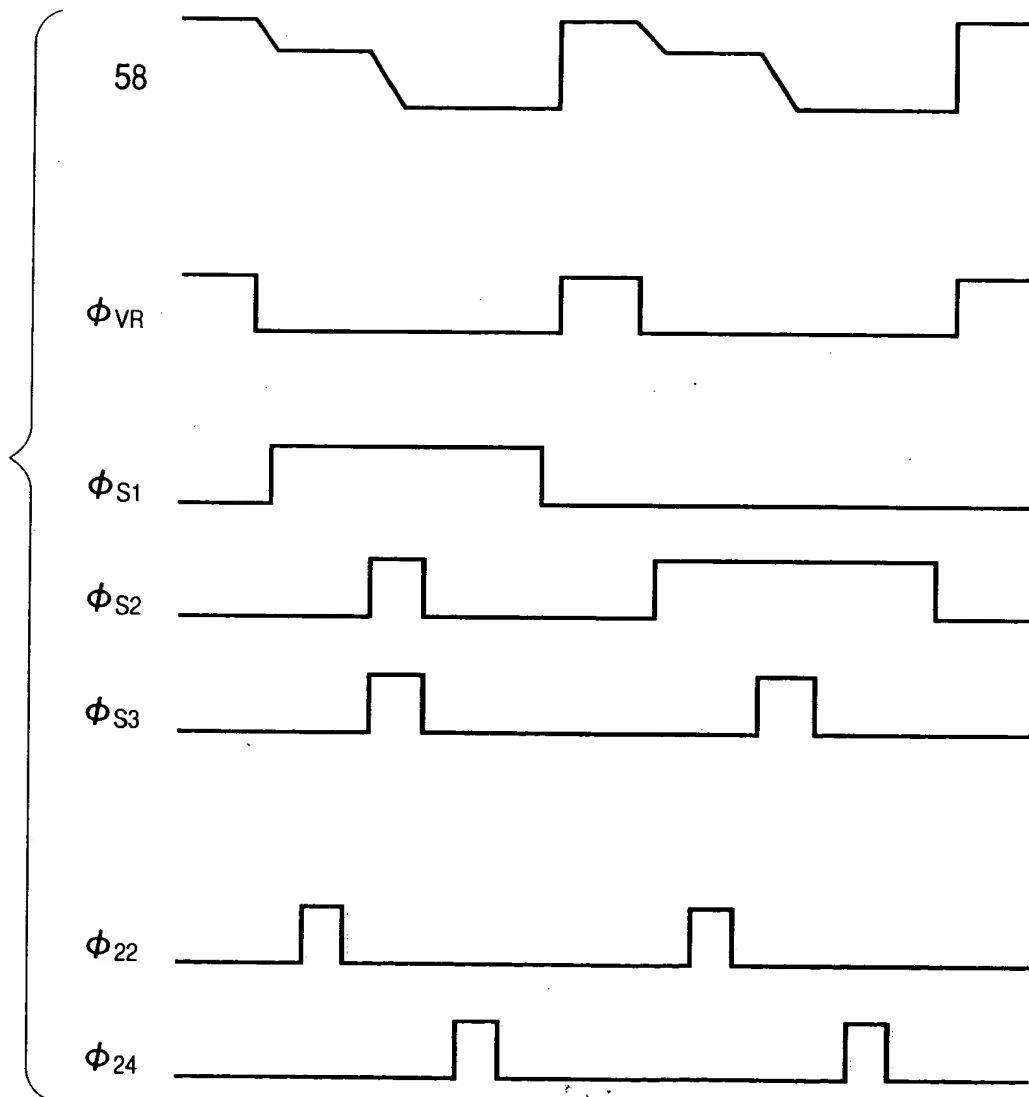
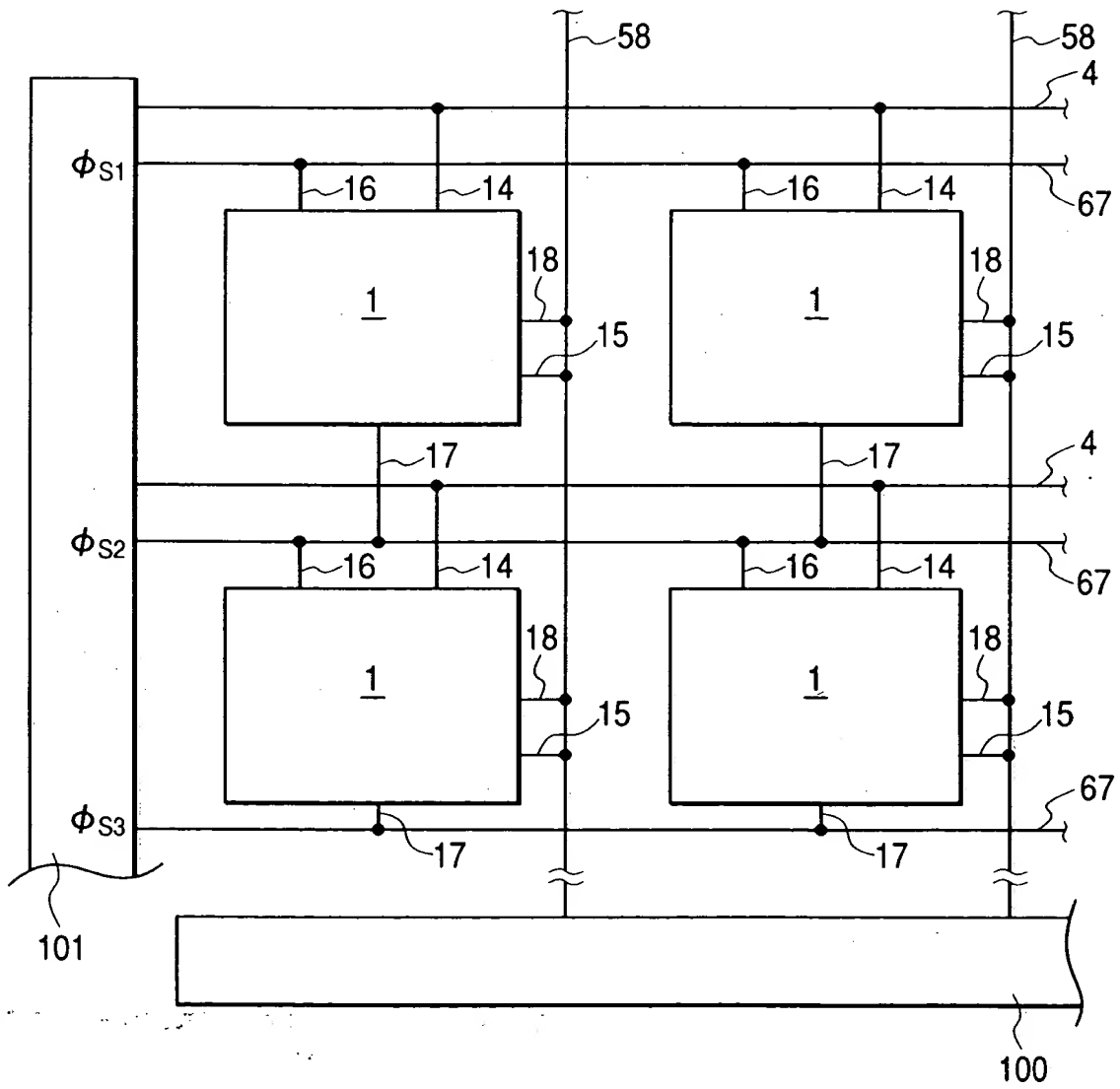
FIG. 19

FIG. 20



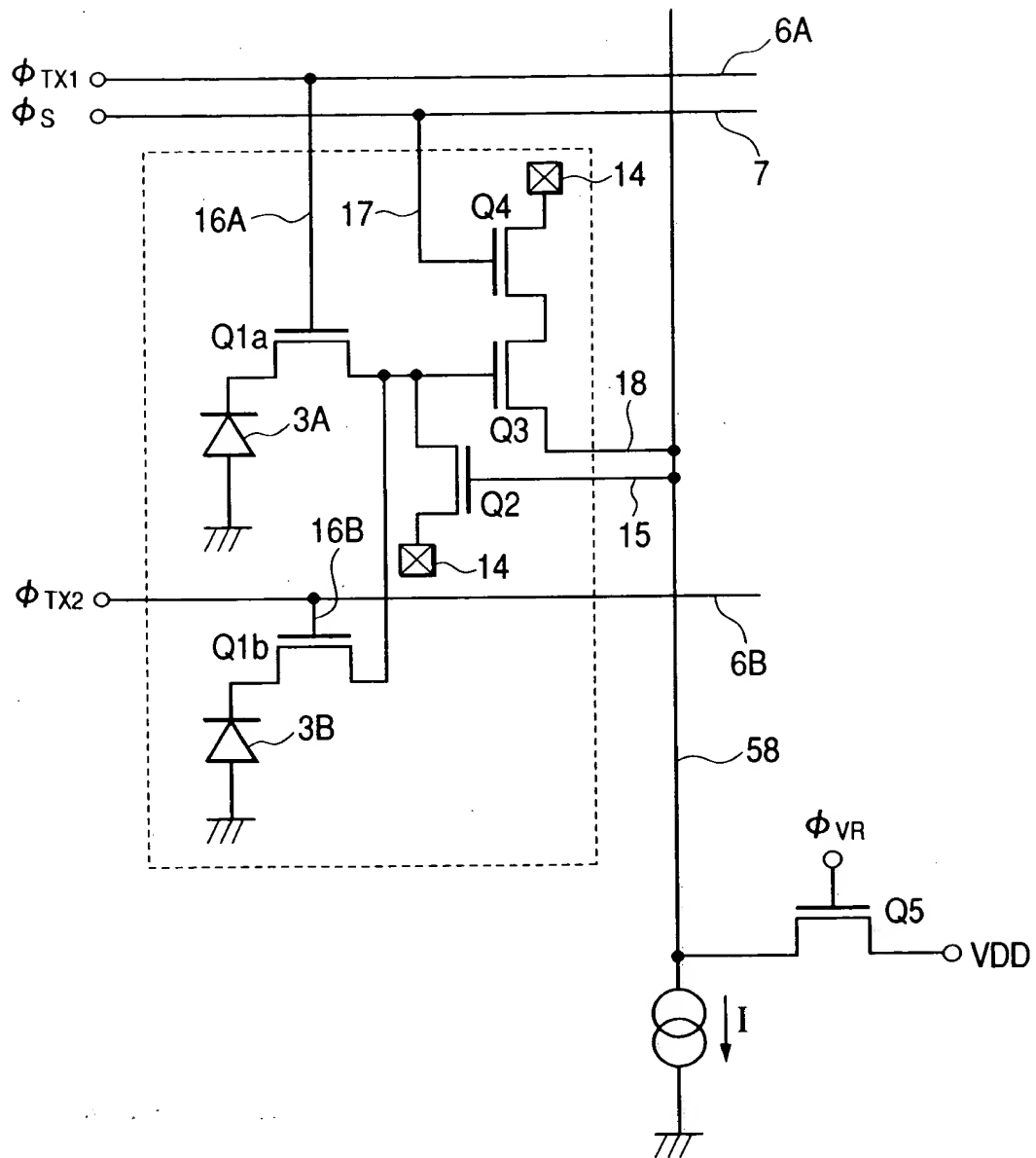
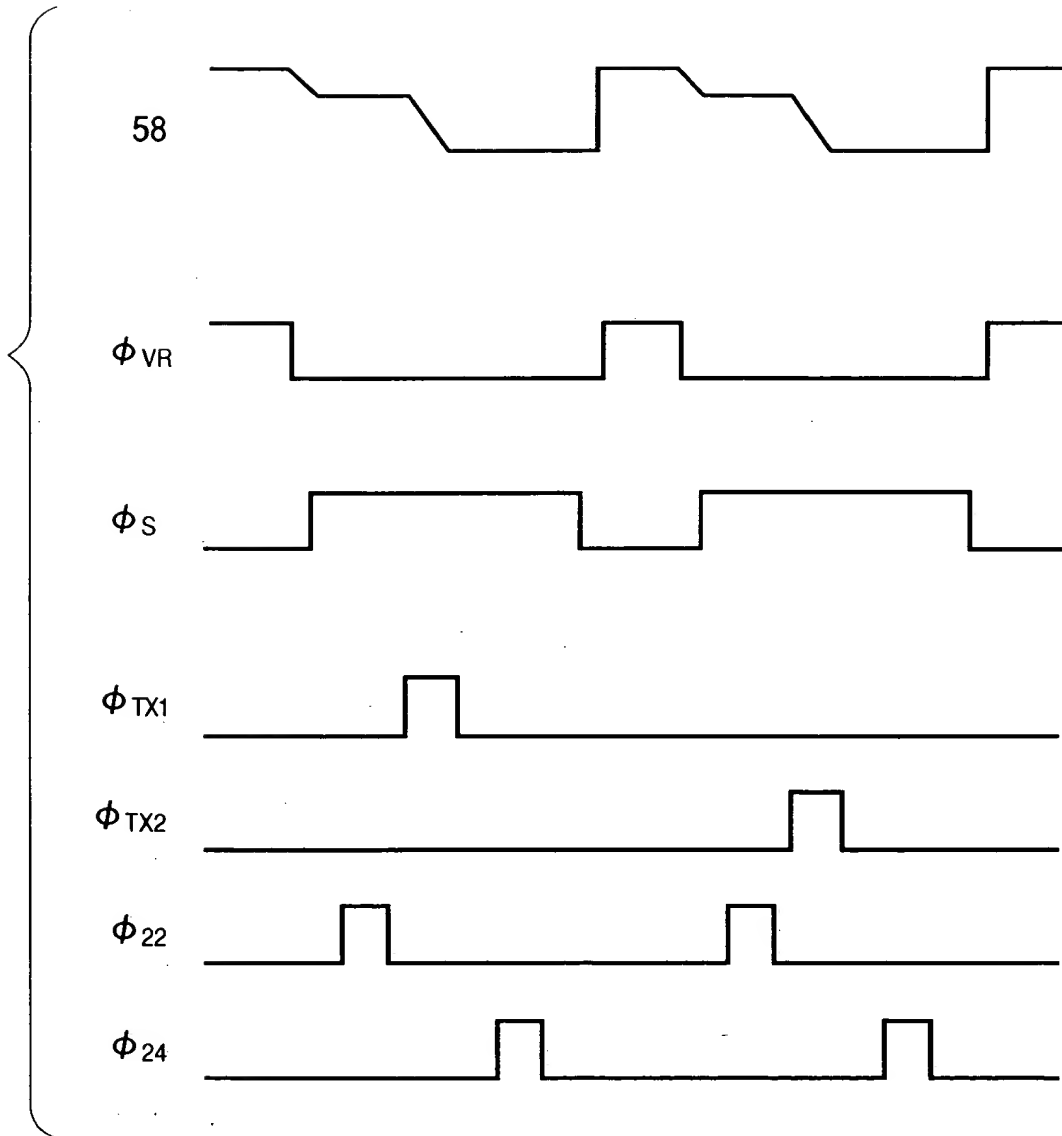
[illegible]

FIG. 22

The diagram illustrates a semiconductor device 100, which is a 2x2 array of unit cells. Each unit cell contains a 1T1R (one transistor, one resistor) structure. The transistors are labeled 1A and 1B, and the storage capacitor is labeled 2. The access transistors 1A and 1B are connected to word lines 4 and bit lines 7, respectively. The storage capacitor 2 is connected to a bit line 7 and a word line 4. The device is connected to a peripheral circuit 101 on the left and a control line 58 at the bottom. The bit lines are labeled 14, 15, 16A, 16B, 17, and 18. The word lines are labeled 1A, 1B, and 2.

FIG. 24

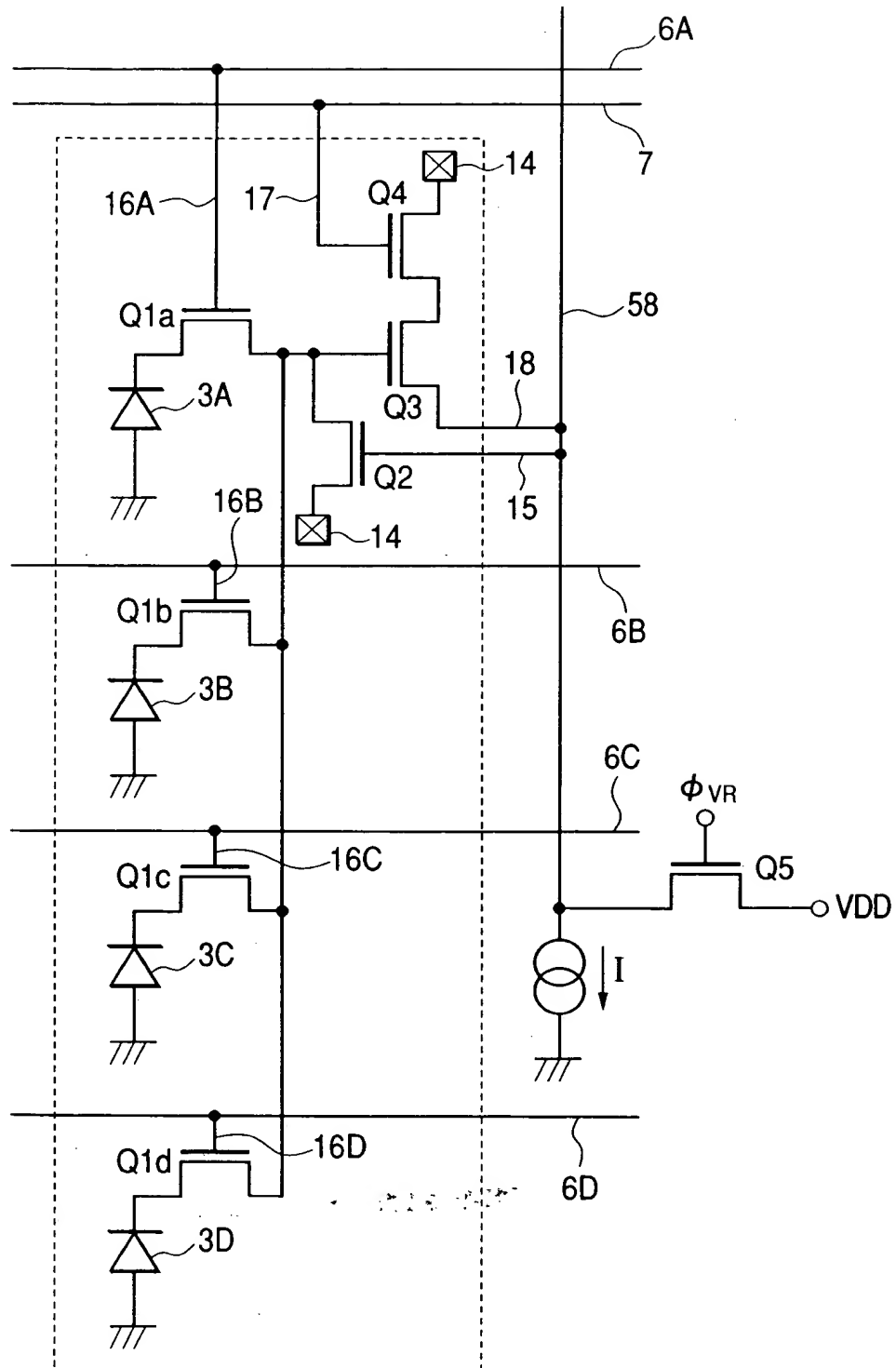


FIG. 25

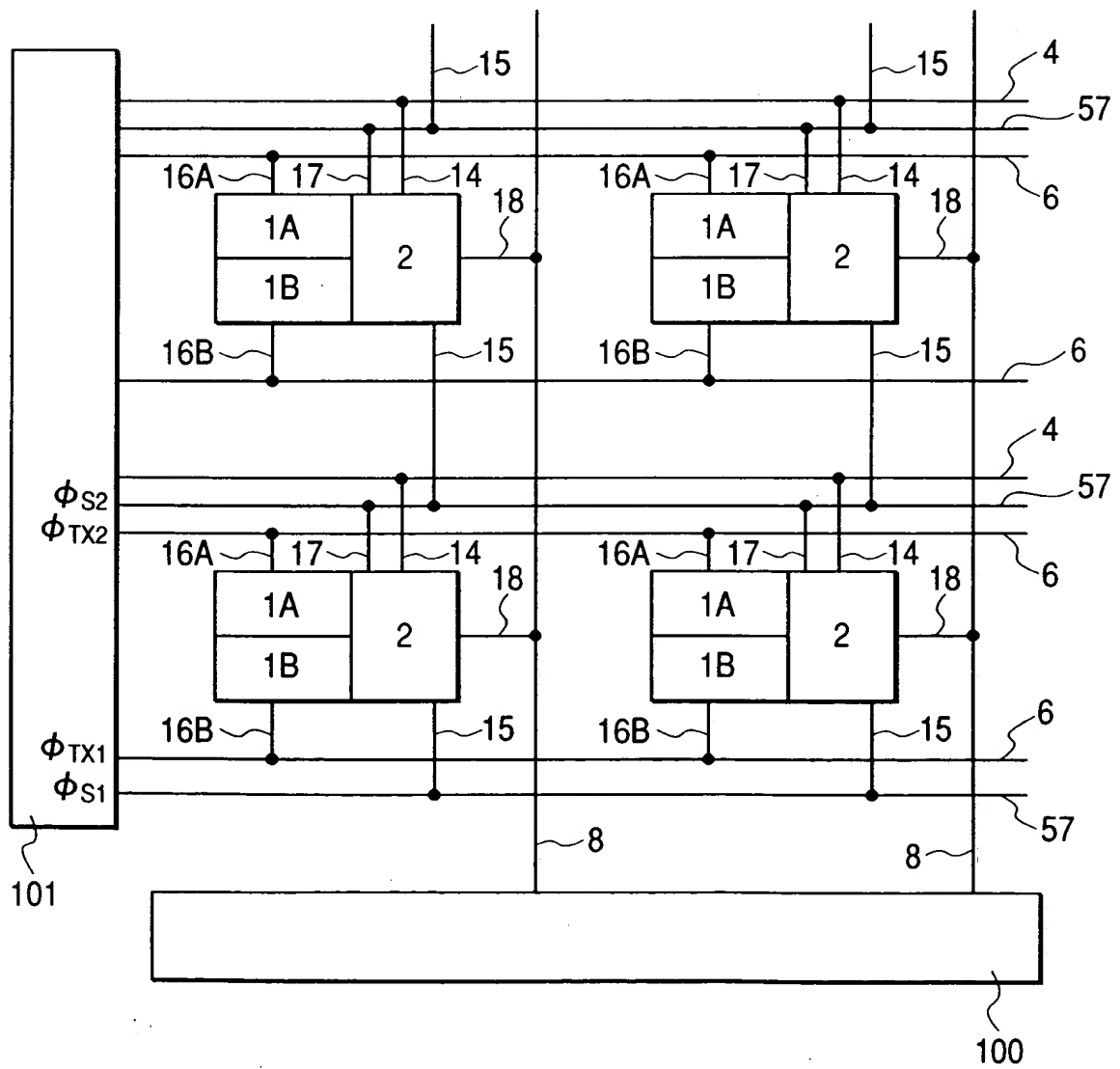


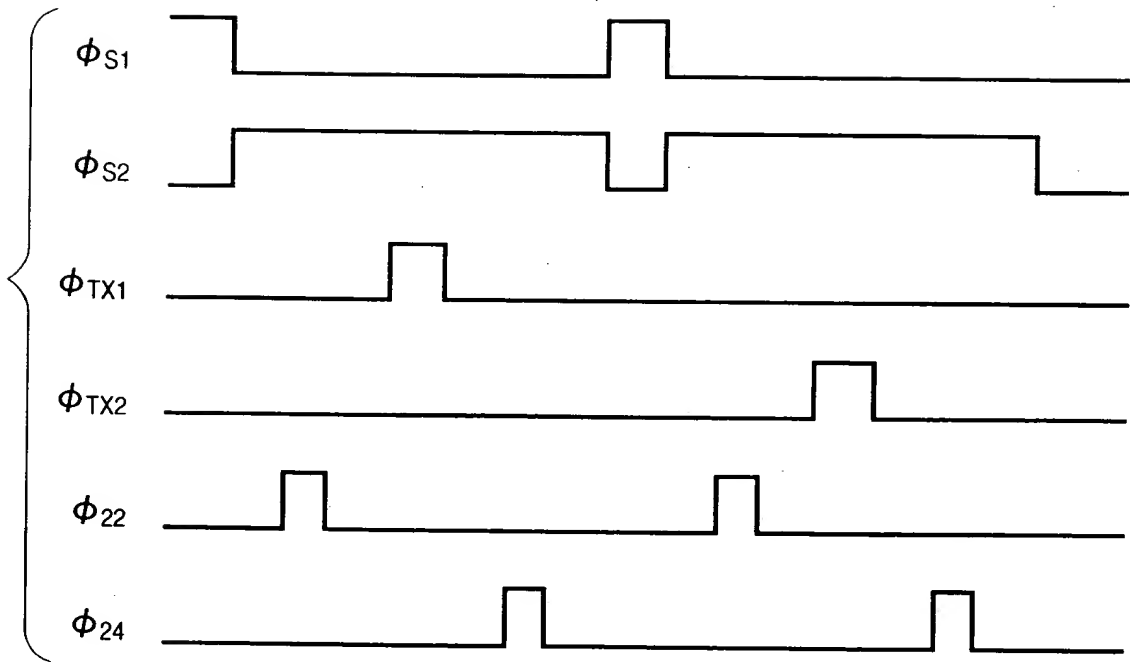
FIG. 26

FIG. 27

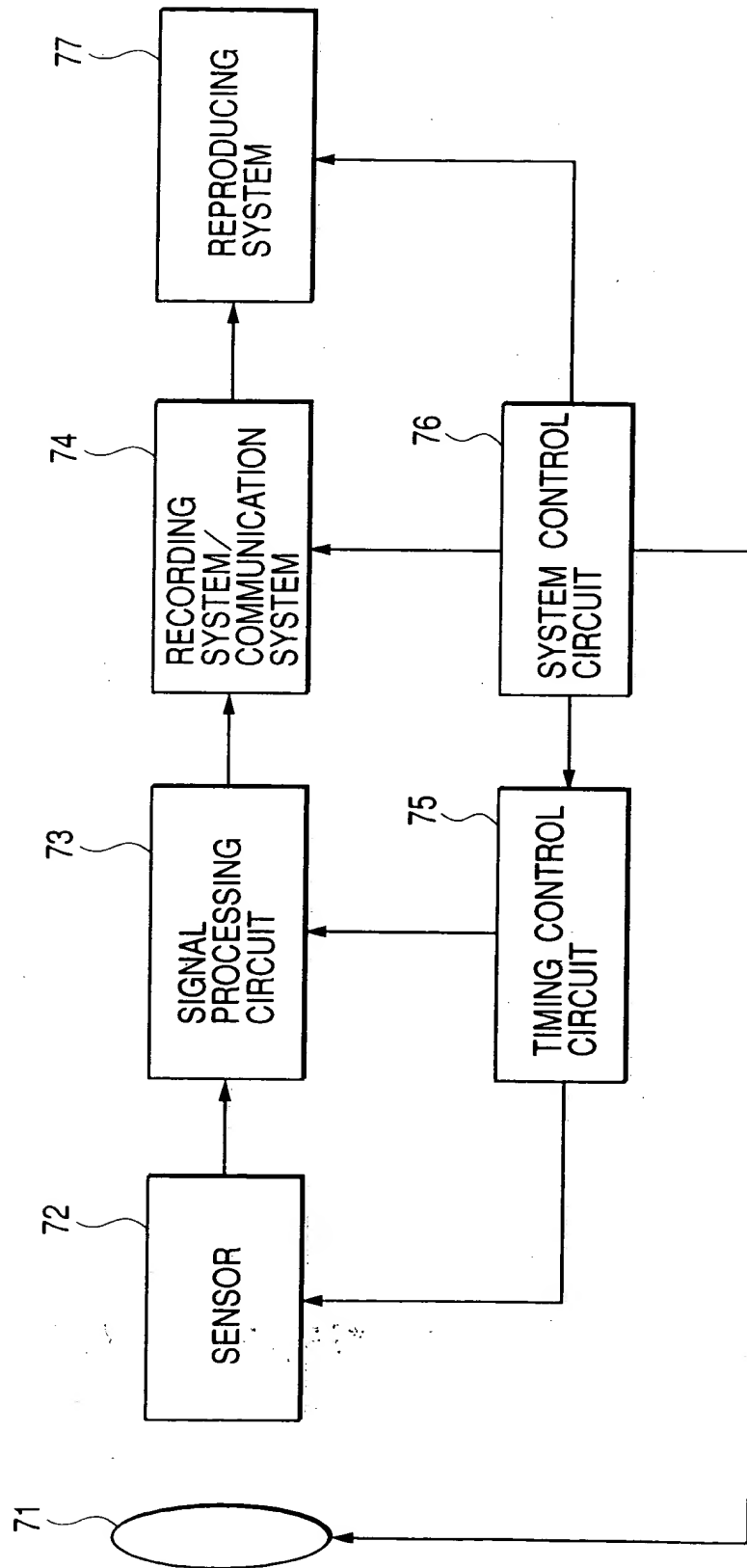


FIG. 28 PRIOR ART

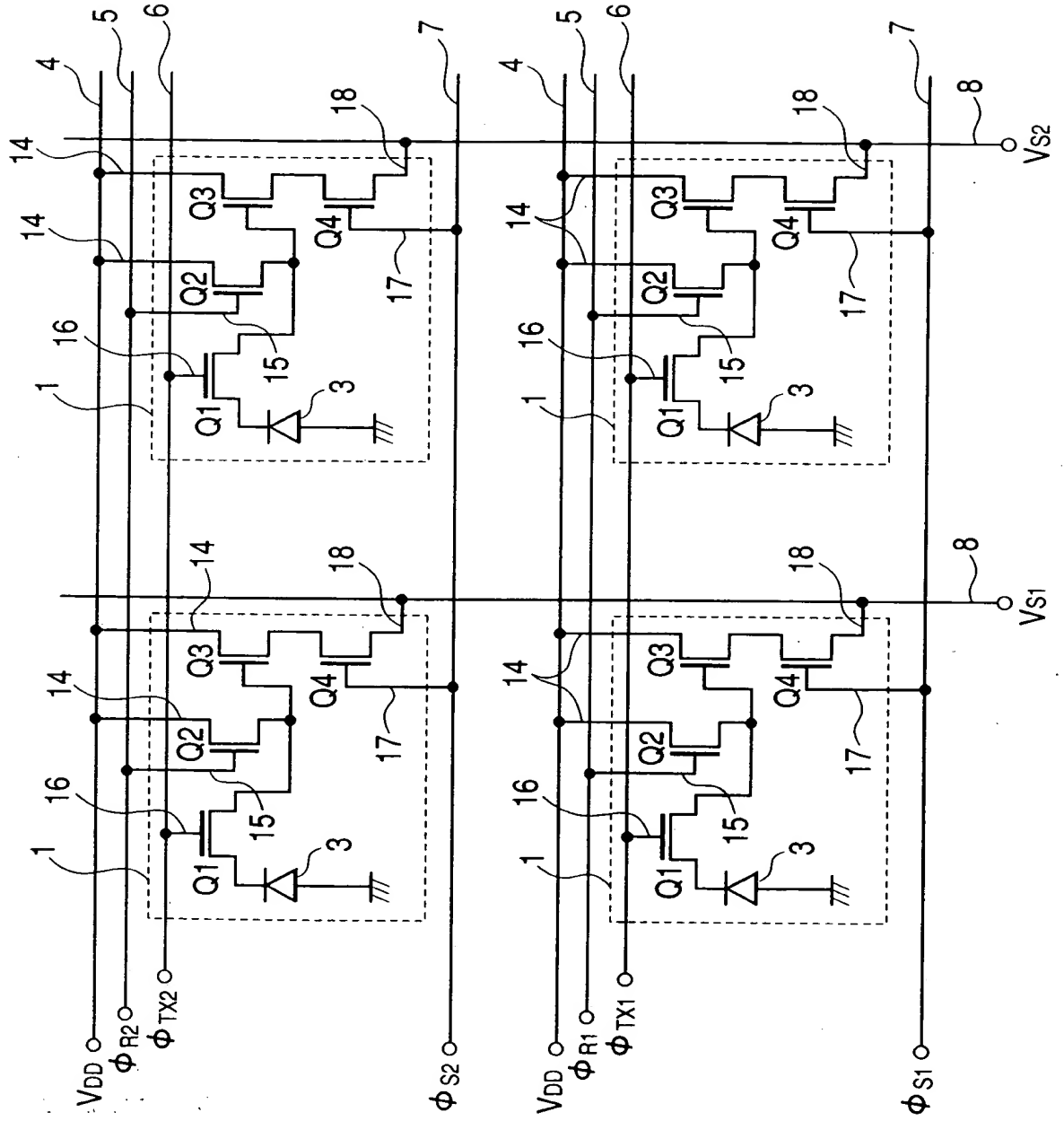


FIG. 29

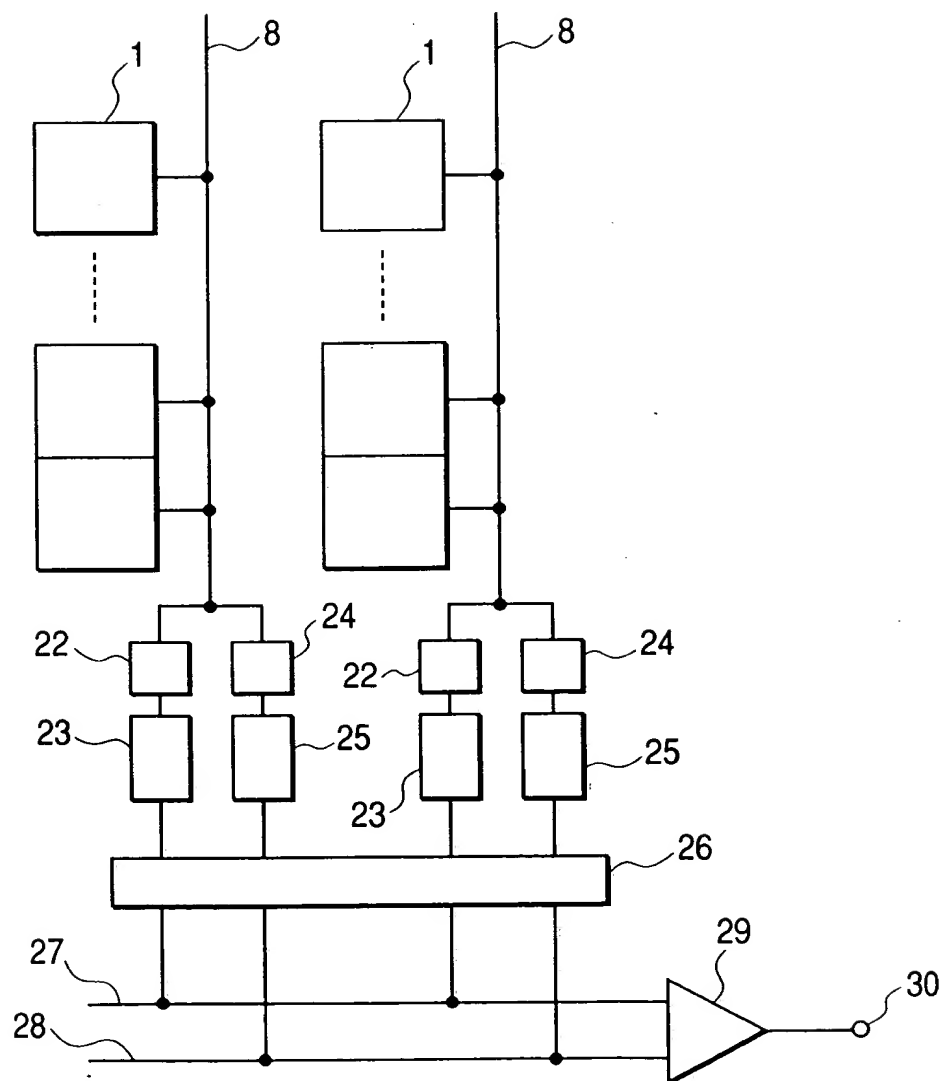


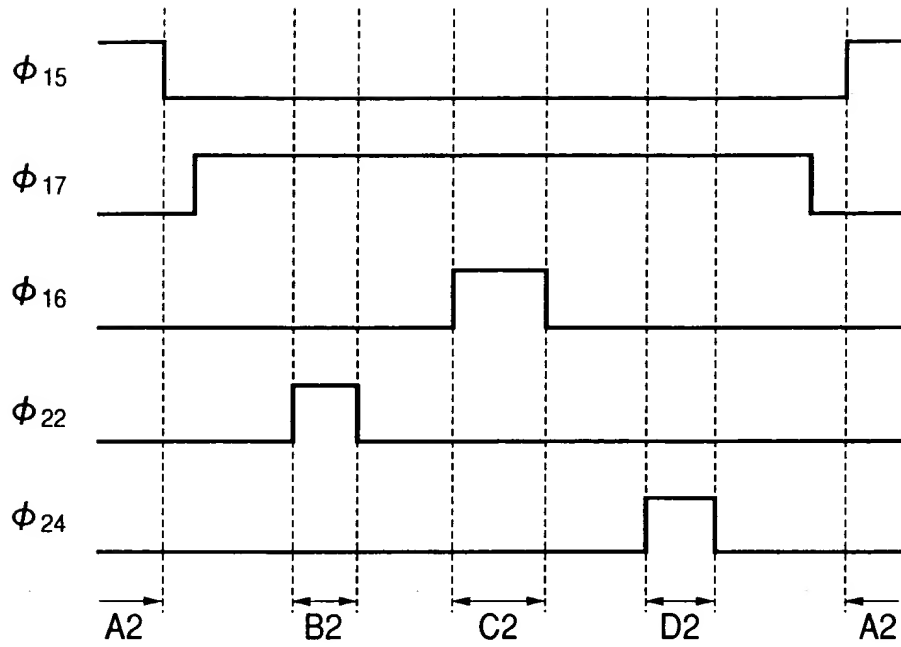
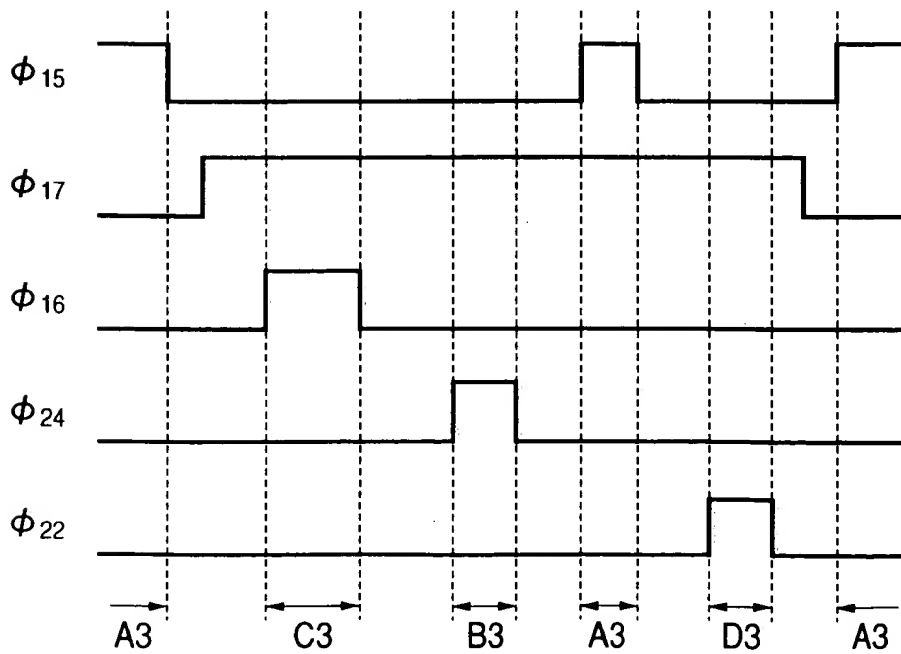
FIG. 30*FIG. 31*

FIG. 32

	PERIOD A	PERIOD B	PERIOD C	PERIOD D
n TH ROW SELECTING SWITCH LINE	—	ON	—	ON
n TH ROW RESET SWITCH LINE	ON	OFF *	OFF *	OFF *
n TH ROW TRANSFER SWITCH LINE	OFF	OFF	ON	OFF
OUTPUT LINE	—	float	—	float
n-1 TH ROW SELECTING SWITCH LINE	—	OFF	—	OFF
n-1 TH ROW RESET SWITCH LINE	—	—	—	—
n-1 TH ROW TRANSFER SWITCH LINE	—	—	—	—
n+1 TH ROW SELECTING SWITCH LINE	—	OFF	—	OFF
n+1 TH ROW RESET SWITCH LINE	—	—	—	—
n+1 TH ROW TRANSFER SWITCH LINE	OFF	OFF	OFF	OFF

FIG. 33